

# IRFB20N50KPbF

**SMPS MOSFET**      HEXFET® Power MOSFET

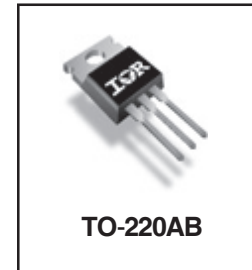
### Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits
- Lead-Free

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> typ.</b>	<b>I<sub>D</sub></b>
<b>500V</b>	<b>0.21Ω</b>	<b>20A</b>

### Benefits

- Low Gate Charge Q<sub>g</sub> results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Low R<sub>DS(on)</sub>



### Absolute Maximum Ratings

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	20	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	12	
I <sub>DM</sub>	Pulsed Drain Current ①	80	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	280	W
	Linear Derating Factor	2.2	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	6.9	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 150	
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case )	300	°C
	Mounting Torque, 6-32 or M3 screw	10	N

### Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	330	mJ
I <sub>AR</sub>	Avalanche Current④	—	20	A
E <sub>AR</sub>	Repetitive Avalanche Energy④	—	28	mJ

### Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	0.45	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient	—	58	

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International  
IR Rectifier

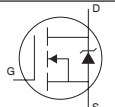
## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.61	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.21	0.25	$\Omega$	$V_{GS} = 10V, I_D = 12A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	50	$\mu A$	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250	$\mu A$	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -30V$

## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	11	—	—	S	$V_{DS} = 50V, I_D = 12A$
$Q_g$	Total Gate Charge	—	—	110	nC	$I_D = 20A$
$Q_{gs}$	Gate-to-Source Charge	—	—	33		$V_{DS} = 400V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	54		$V_{GS} = 10V, \text{See Fig. 6 and 13}$ ④
$t_{d(on)}$	Turn-On Delay Time	—	22	—	ns	$V_{DD} = 250V$
$t_r$	Rise Time	—	74	—		$I_D = 20A$
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		$R_G = 7.5\Omega$
$t_f$	Fall Time	—	33	—		$V_{GS} = 10V, \text{See Fig. 10}$ ④
$C_{iss}$	Input Capacitance	—	2870	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	320	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	34	—		$f = 1.0\text{MHz}, \text{See Fig. 5}$
$C_{oss}$	Output Capacitance	—	3480	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	85	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	160	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

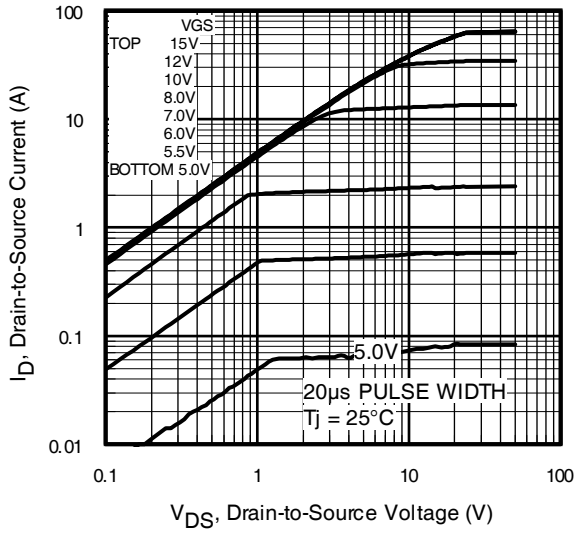
## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	20	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	80		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 20A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	520	780	ns	$T_J = 25^\circ\text{C}, I_F = 20A$
$Q_{rr}$	Reverse Recovery Charge	—	5.3	8.0	$\mu\text{C}$	$di/dt = 100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

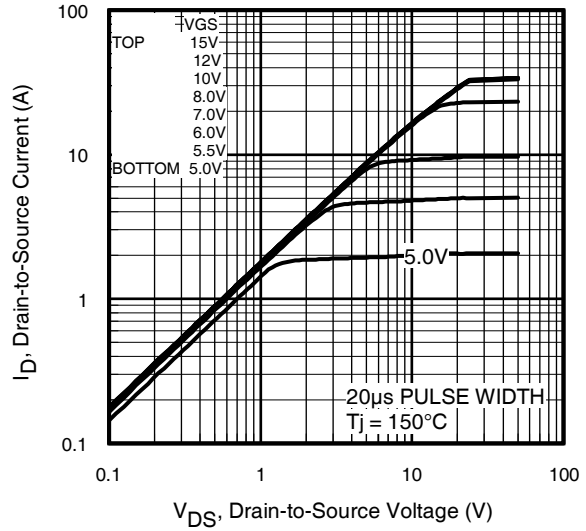
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}, L = 1.6\text{mH}, R_G = 25\Omega, I_{AS} = 20A,$
- ③  $I_{SD} \leq 20A, di/dt \leq 350A/\mu\text{s}, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 400\mu\text{s};$  duty cycle  $\leq 2\%.$

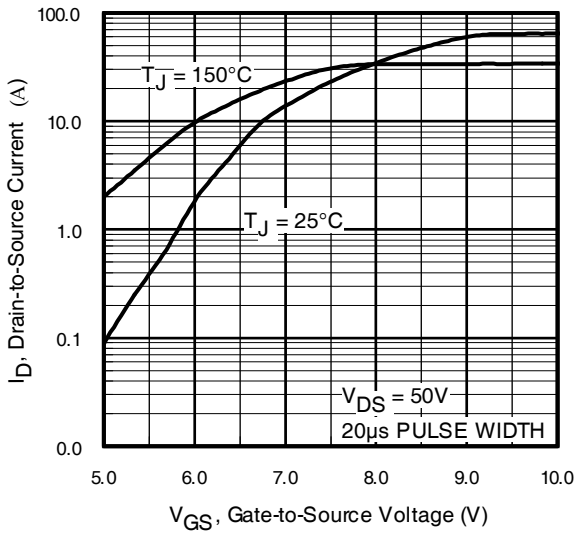
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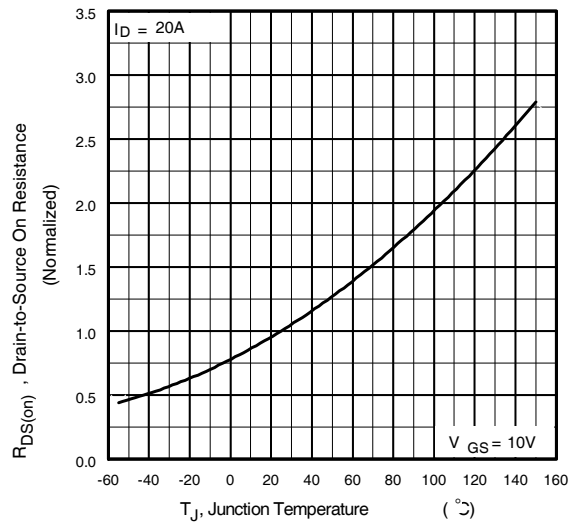
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

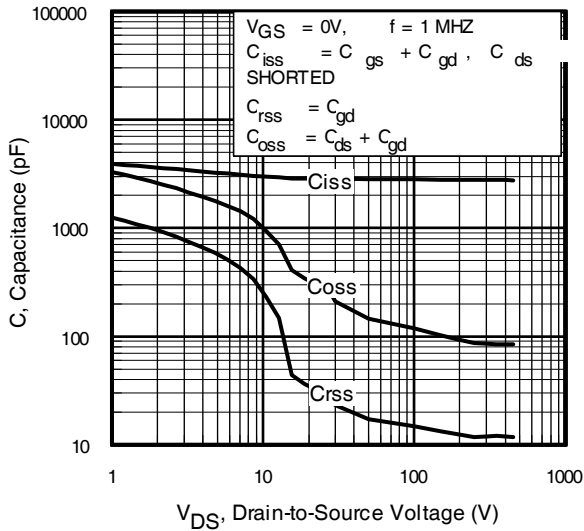


**Fig 3.** Typical Transfer Characteristics

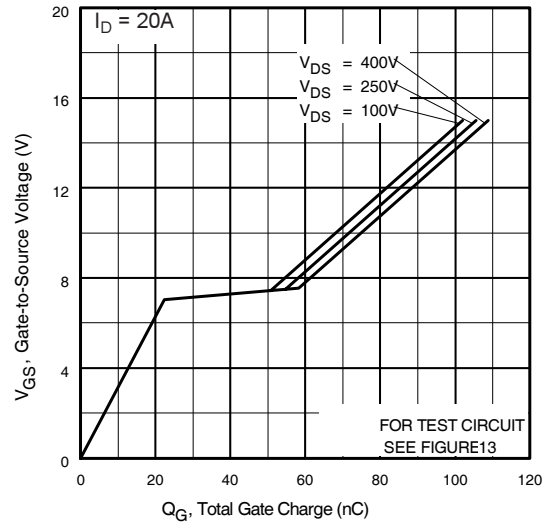


**Fig 4.** Normalized On-Resistance Vs. Temperature

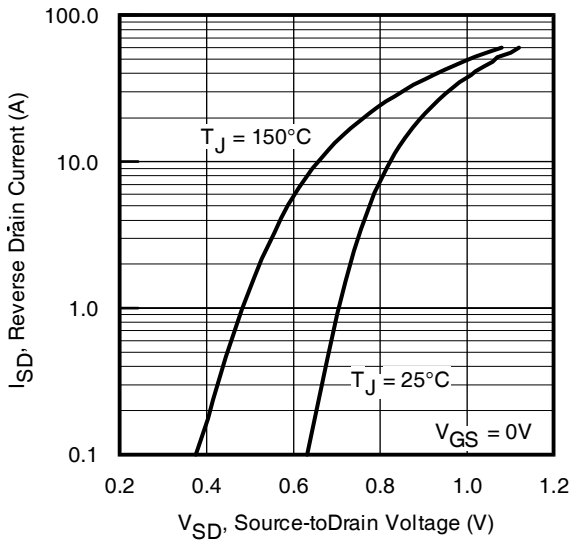
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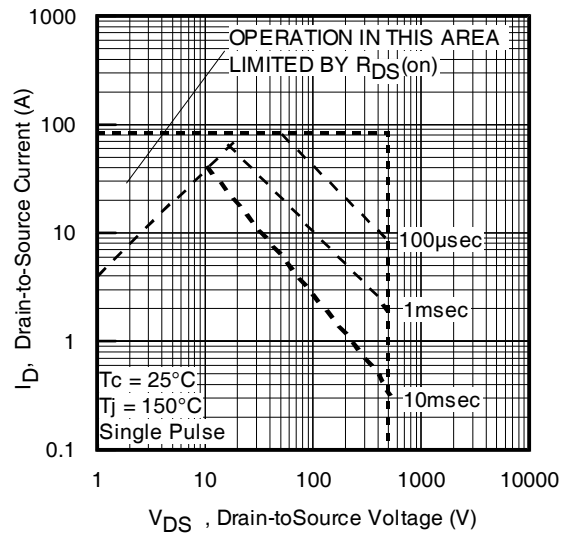
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



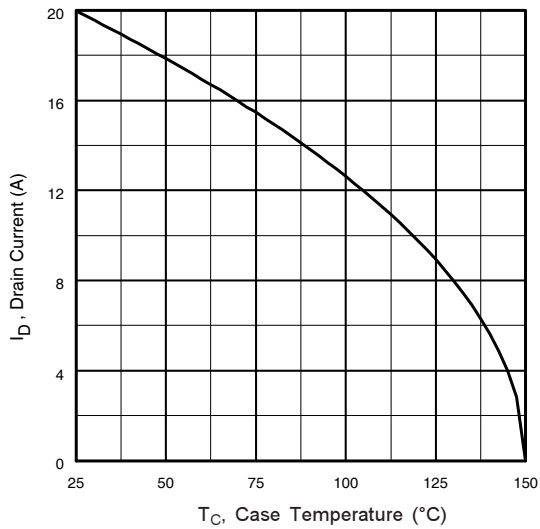
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



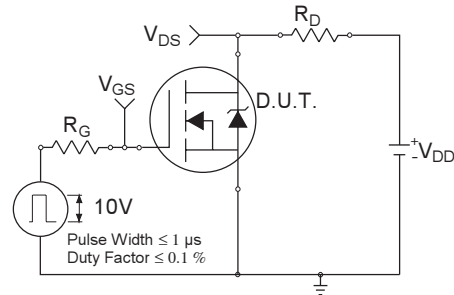
**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area



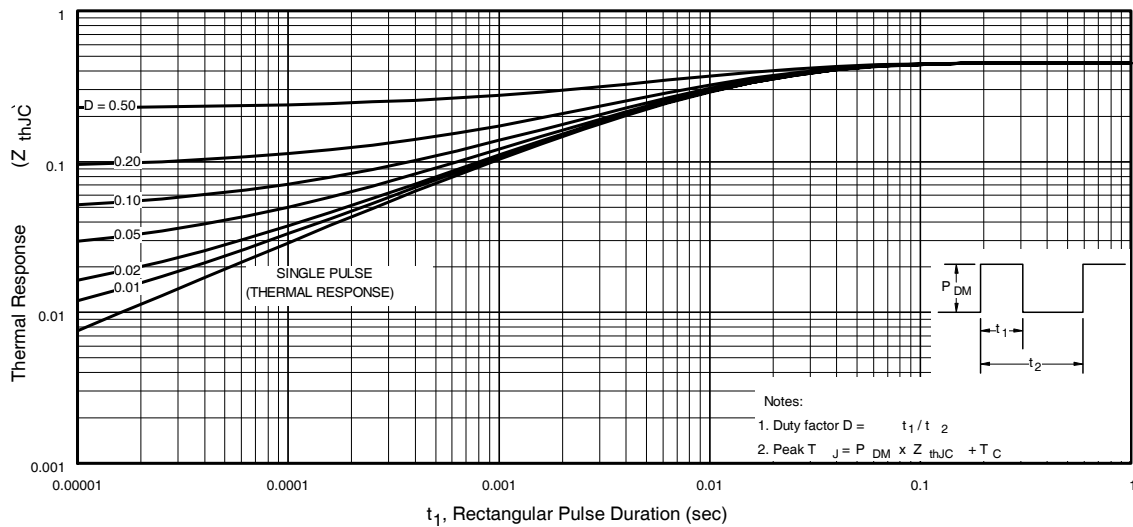
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

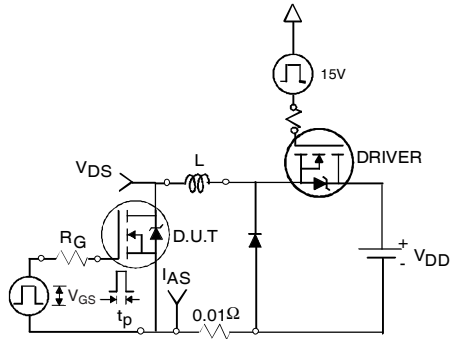


**Fig 10b.** Switching Time Waveforms

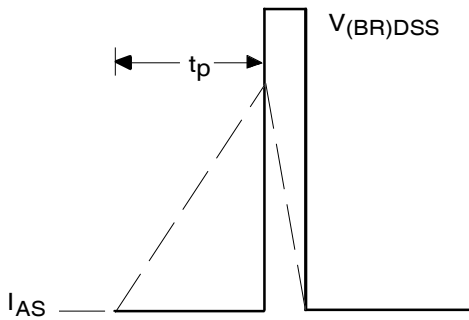


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

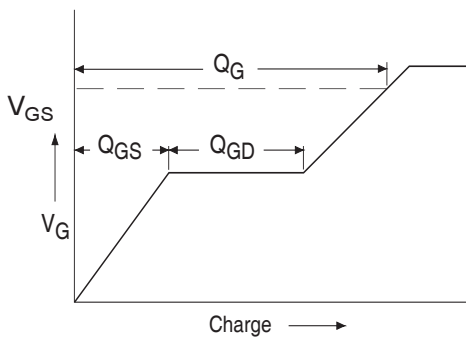
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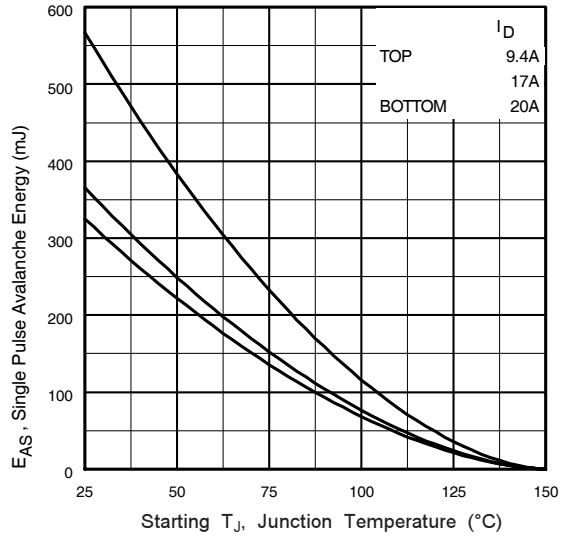
**Fig 12a.** Unclamped Inductive Test Circuit



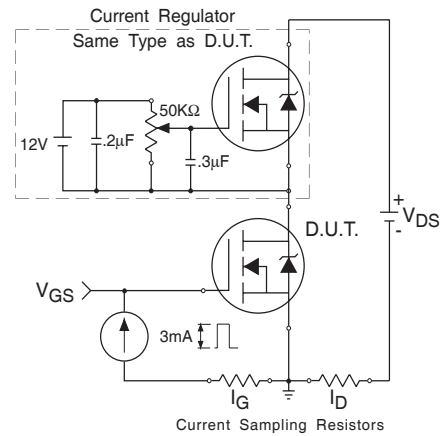
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

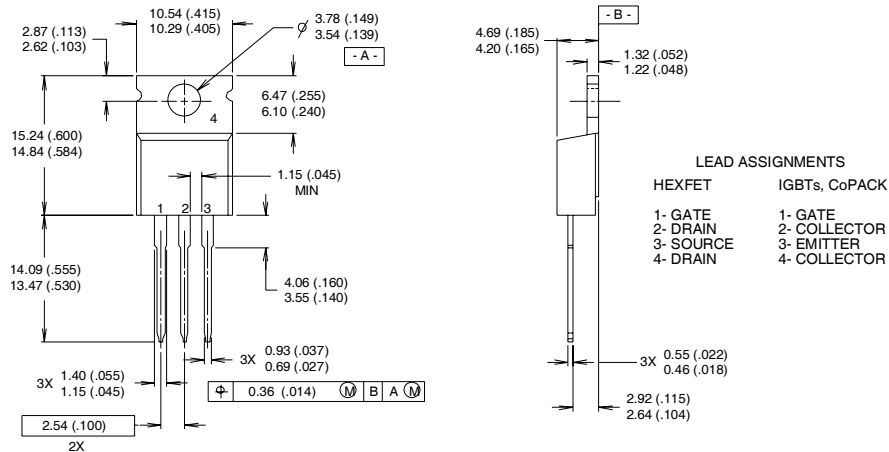
**Fig 14.** For N-Channel HEXFETS

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International  
**IR** Rectifier

## TO-220AB Package Outline

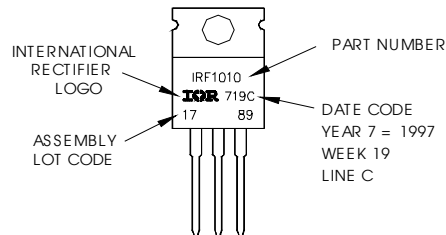
Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH
  - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
  - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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